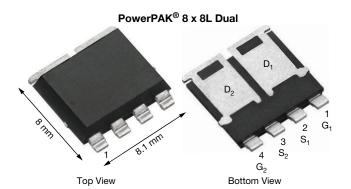
SQJQ900E

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Vishay Siliconix

Automotive Dual N-Channel 40 V (D-S) 175 °C MOSFET



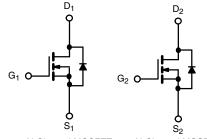
PRODUCT SUMMARY	
V _{DS} (V)	40
$R_{DS(on)}$ (Ω) at V_{GS} = 10 V	0.0039
$R_{DS(on)}$ (Ω) at V_{GS} = 4.5 V	0.0047
I _D (A) per leg	100
Configuration	Dual
Package	PowerPAK 8 x 8L

FEATURES

- TrenchFET[®] power MOSFET
- AEC-Q101 qualified
- 100 % R_q and UIS tested
- Fully lead (Pb)-free device
- Material categorization: for definitions of compliance please see <u>www.vishay.com/doc?99912</u>



KONS COMPLIANT HALOGEN



N-Channel MOSFET N-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS (T _C = 25 °C, unles	s otherwise noted	l)	
PARAMETER		SYMBOL	LIMIT	UNIT
Drain-source voltage		V _{DS}	40	V
Gate-source voltage		V _{GS}	± 20	v
Continuous drain current	T _C = 25 °C ^a T _C = 125 °C	I-	100	
Continuous drain current	T _C = 125 °C	I _D	60	
Continuous source current (diode conduction) ^a		I _S	68	А
Pulsed drain current ^b		I _{DM}	400	
Single pulse avalanche current	L = 0.1 mH	I _{AS}	50	
Single pulse avalanche energy	L = 0.1 mm	E _{AS}	125	mJ
Maximum power dissipation ^b	T _C = 25 °C		75	W
Maximum power dissipation ~	T _C = 125 °C	P _D	25	vv
Operating junction and storage temperature range	ge	T _J , T _{stg}	-55 to +175	°C
Soldering recommendations (peak temperature) ^{d, e}			260	C

THERMAL RESISTANCE RATINGS				
PARAMETER		SYMBOL	LIMIT	UNIT
Junction-to-ambient	PCB mount ^c	R _{thJA}	80	°C/W
Junction-to-case (drain)		R _{thJC}	2	0/10

Notes

a. Package limited

b. Pulse test; pulse width $\leq 300~\mu s,~duty~cycle \leq 2~\%$

c. When mounted on 1" square PCB (FR4 material)

d. See solder profile (<u>www.vishay.com/doc?73257</u>). The PowerPAK 8 x 8L is a leadless package. The end of the lead terminal is exposed copper (not plated) as a result of the singulation process in manufacturing. A solder fillet at the exposed copper tip cannot be guaranteed and is not required to ensure adequate bottom side solder interconnection

e. Rework conditions: manual soldering with a soldering iron is not recommended for leadless components

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SQJQ900E

PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNIT
Static				•	•		
Drain-source breakdown voltage	V _{DS}	V _{GS}	= 0, I _D = 250 μA	40	-	-	v
Gate-source threshold voltage	V _{GS(th)}	V _{DS} =	= V _{GS} , I _D = 250 μΑ	1.5	2	2.5	v
Gate-source leakage	I _{GSS}	V _{DS} =	$0 \text{ V}, \text{V}_{\text{GS}} = \pm 20 \text{ V}$	-	-	± 100	nA
		$V_{GS} = 0 V$	V _{DS} = 20 V	-	-	1	
Zero gate voltage drain current	I _{DSS}	$V_{GS} = 0 V$	$V_{DS} = 40 \text{ V}, \text{ T}_{J} = 125 ^{\circ}\text{C}$	-	-	50	μA
		$V_{GS} = 0 V$	$V_{DS} = 40 \text{ V}, \text{ T}_{J} = 175 ^{\circ}\text{C}$	-	-	150	
On-state drain current ^a	I _{D(on)}	V _{GS} = 10 V	$V_{DS} \ge 5 V$	40	-	-	Α
		V _{GS} = 10 V	I _D = 20 A	-	0.0034	0.0039	
Drain actures an state registeres a	Р	$V_{GS} = 4.5 V$	I _D = 10 A	-	0.0039	0.0047	
Drain-source on-state resistance ^a	R _{DS(on)}	V _{GS} = 10 V	I _D = 20 A, T _J = 125 °C	-	-	0.0074	Ω
		V _{GS} = 10 V	I _D = 20 A, T _J = 175 °C	-	-	0.0091	
Forward transconductance b		V _{DS}	= 15 V, I _D = 15 A	-	105	-	S
Dynamic ^b		-			-		
Input capacitance	C _{iss}			-	4695	5900	
Output capacitance	C _{oss}	$V_{GS} = 0 V$	V_{DS} = 20 V, f = 1 MHz	-	637	800	pF
Reverse transfer capacitance	C _{rss}			-	259	330	
Total gate charge ^c	Qg			-	85	120	
Gate-source charge ^c	Q _{gs}	$V_{GS} = 10 \text{ V}$	$V_{DS} = 20 \text{ V}, I_D = 40 \text{ A}$	-	10	-	nC
Gate-drain charge ^c	Q _{gd}			-	12	-	
Gate resistance	Rg		f = 1 MHz	0.7	1.5	3.0	Ω
Turn-on delay time ^c	t _{d(on)}			-	14	30	
Rise time ^c	t _r	V _{DD} =	= 20 V, R _L = 0.5 Ω	-	7.5	15	
Turn-off delay time ^c	t _{d(off)}	$I_D \cong 40 \text{ A},$	$V_{GEN} = 10 \text{ V}, \text{ R}_{g} = 1 \Omega$	-	30	60	ns
Fall time ^c	t _f			-	14	30	
Source-Drain Diode Ratings and Cha	racteristics ^b						
Pulsed current ^a	I _{SM}			-	-	200	Α
Forward voltage	V _{SD}	IF	= 40 A, V _{GS} = 0	-	1	1.2	V

Notes

a. Pulse test; pulse width \leq 300 µs, duty cycle \leq 2 %

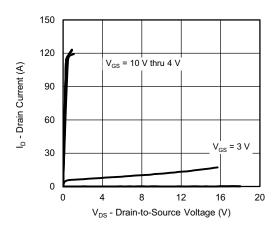
b. Guaranteed by design, not subject to production testing

c. Independent of operating temperature

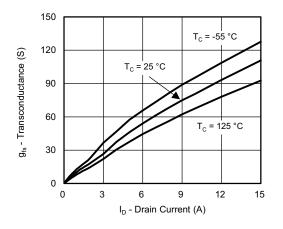
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.



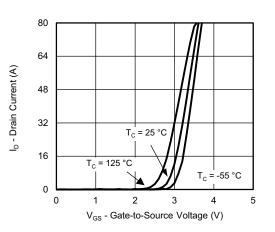
TYPICAL CHARACTERISTICS ($T_A = 25 \text{ °C}$, unless otherwise noted)



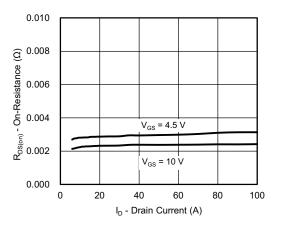
Output Characteristics



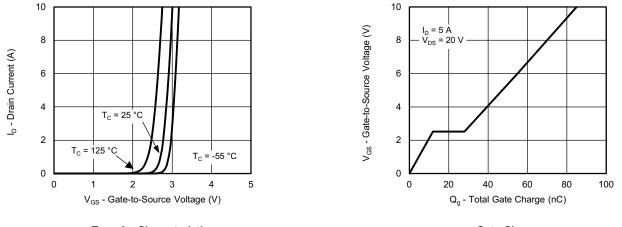
Transconductance



Transfer Characteristics



On-Resistance vs. Drain Current



Transfer Characteristics



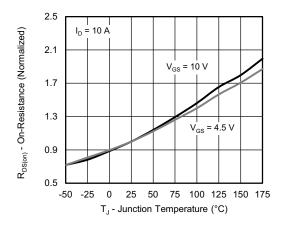
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3 tions. contact: automostechsur Document Number: 62796

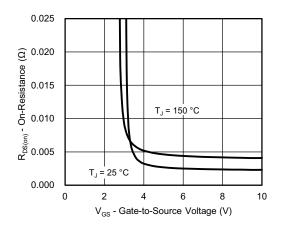
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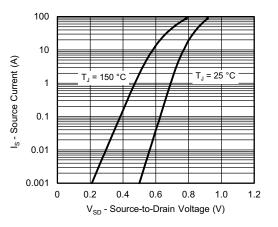
TYPICAL CHARACTERISTICS ($T_A = 25 \text{ °C}$, unless otherwise noted)



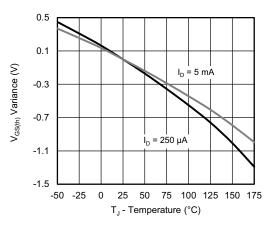
On-Resistance vs. Junction Temperature

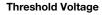


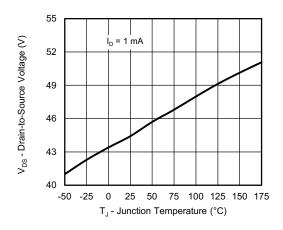
On-Resistance vs. Gate-to-Source Voltage



Source Drain Diode Forward Voltage







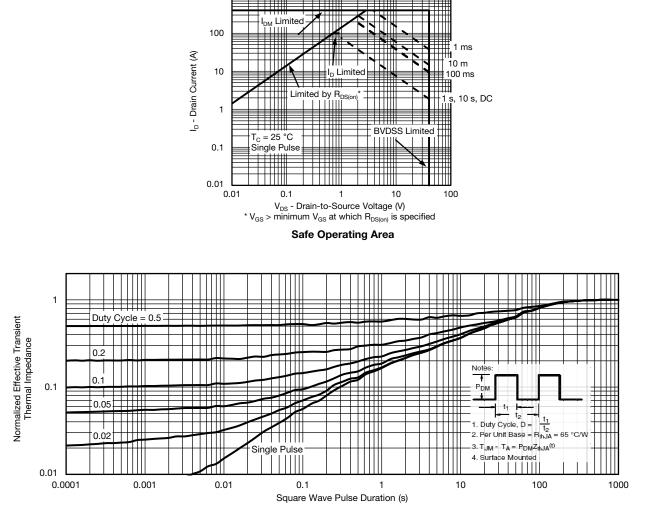
Drain Source Breakdown vs. Junction Temperature

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THERMAL RATINGS ($T_A = 25 \text{ °C}$, unless otherwise noted)

1000

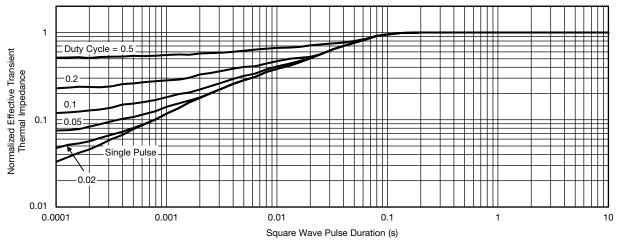


Normalized Thermal Transient Impedance, Junction-to-Ambient



Document Number: 62796

THERMAL RATINGS ($T_A = 25 \text{ °C}$, unless otherwise noted)





Note

• The characteristics shown in the two graphs

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- Normalized Transient Thermal Impedance Junction to Ambient (25 °C)

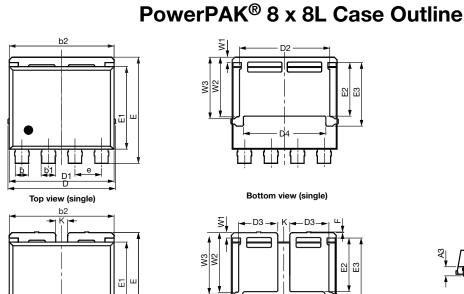
- Normalized Transient Thermal Impedance Junction to Case (25 °C)

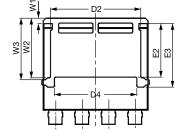
are given for general guidelines only to enable the user to get a "ball park" indication of part capabilities. The data are extracted from single pulse transient thermal impedance characteristics which are developed from empirical measurements. The latter is valid for the part mounted on printed circuit board - FR4, size 1" x 1" x 0.062", double sided with 2 oz. copper, 100 % on both sides. The part capabilities can widely vary depending on actual application parameters and operating conditions.

Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package/tape drawings, part marking, and reliability data, see www.vishay.com/ppg?62796.

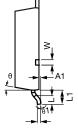
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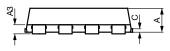




Bottom view (single)



0.25 gauge line





¥, D3 🗕 _D3 W3 W2 Ш

Bottom view (dual)

DIM.		MILLIMETERS			INCHES	
DIM.	MIN.	MIN. NOM.		MIN.	NOM.	MAX.
А	1.70	1.80	1.90	0.067	0.071	0.075
A1	0.00	0.08	0.13	0.000	0.003	0.005
A3	0.55	0.62	0.70	0.022	0.024	0.028
b	0.92	1.00	1.08	0.036	0.039	0.043
b1	1.02	1.10	1.18	0.040	0.043	0.046
b2	7.80	7.90	8.00	0.307	0.311	0.315
С	0.20	0.25	0.30	0.008	0.010	0.012
D	8.00	8.10	8.25	0.315	0.319	0.325
D1	7.80	7.90	8.00	0.307	0.311	0.315
D2	6.70	6.80	6.90	0.264	0.268	0.272
D3	2.85	2.95	3.05	0.112	0.116	0.120
D4	6.11	6.21	6.31	0.241	0.244	0.248
е	1.95	2.00	2.05	0.077	0.079	0.081
E	7.90	8.00	8.10	0.311	0.315	0.319
E1	6.12	6.22	6.32	0.241	0.245	0.249
E2	3.94	4.04	4.14	0.140	0.159	0.163
E3	4.69	4.79	4.89	0.185	0.189	0.193
F	0.05	0.10	0.15	0.002	0.004	0.006
L	0.62	0.72	0.82	0.024	0.028	0.032
L1	0.92	1.07	1.22	0.036	0.042	0.048
К	0.80	0.90	1.00	0.031	0.035	0.039
W	0.30	0.40	0.50	0.012	0.016	0.020
W1	0.30	0.40	0.50	0.012	0.016	0.020
W2	4.39	4.49	4.59	0.173	0.177	0.181
W3	4.54	4.64	4.74	0.179	0.183	0.187
θ	6°	10°	14°	6°	10°	14°
θ1	0°	3°	8°	0°	3°	8°
-0891-Rev. A, G: 6026	06-Oct-14					

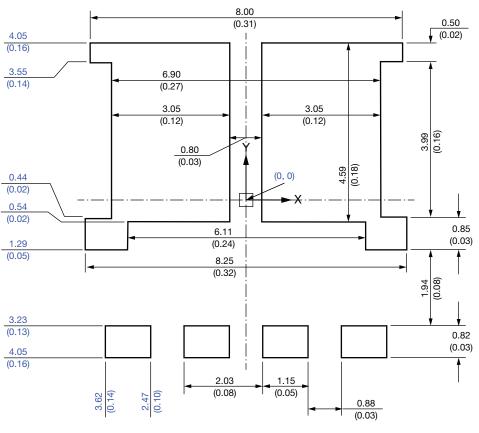
Revision: 06-Oct-14

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Recommended Minimum PADs for PowerPAK® 8 x 8L Dual



Dimensions in millimeters (inches)

Note

• Linear dimensions are in black, the same information is provided in ordinate dimensions which are in blue.



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